

FIG. 1
(PRIOR ART)

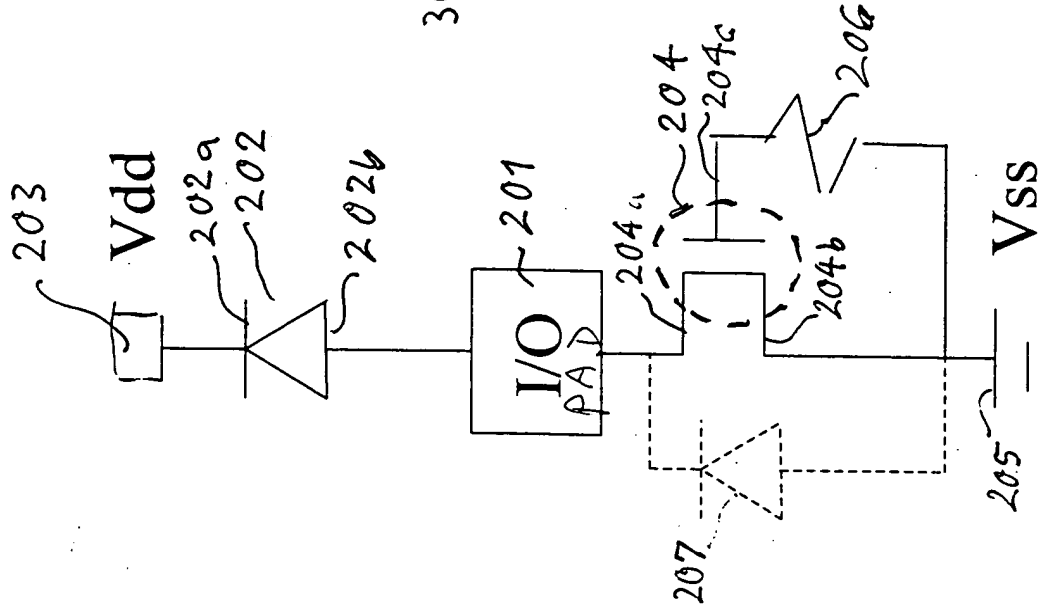


FIG. 2
(PRIOR ART)

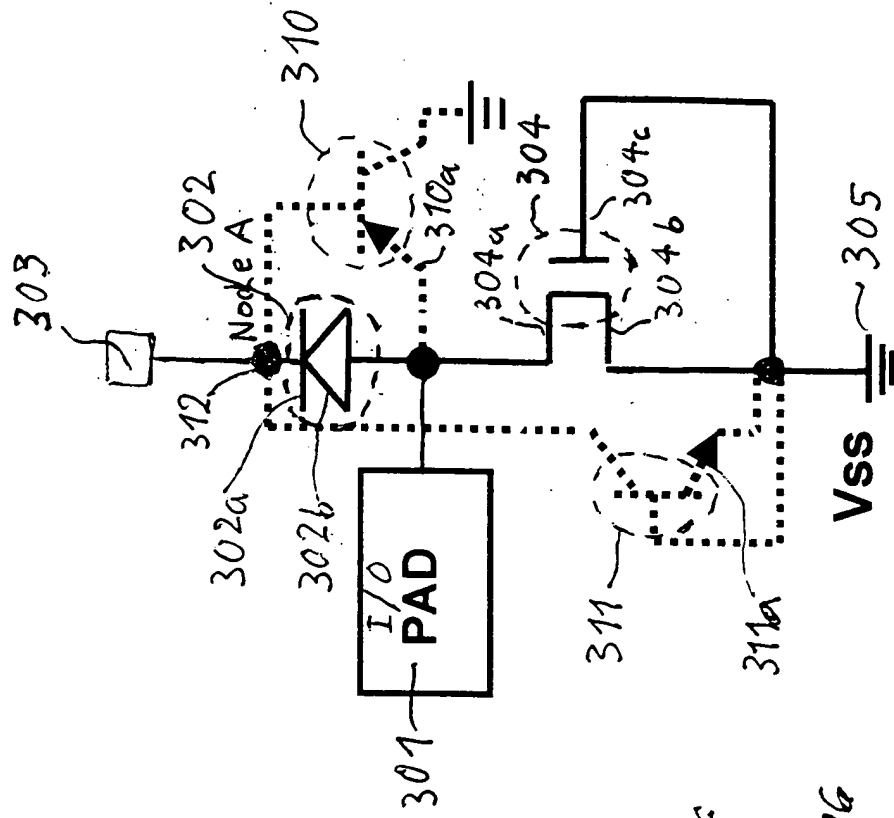


FIG. 3

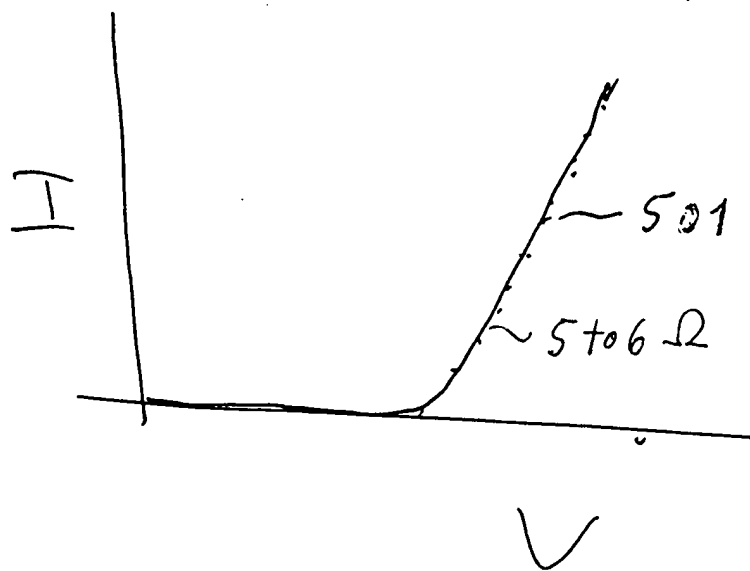


FIG. 5

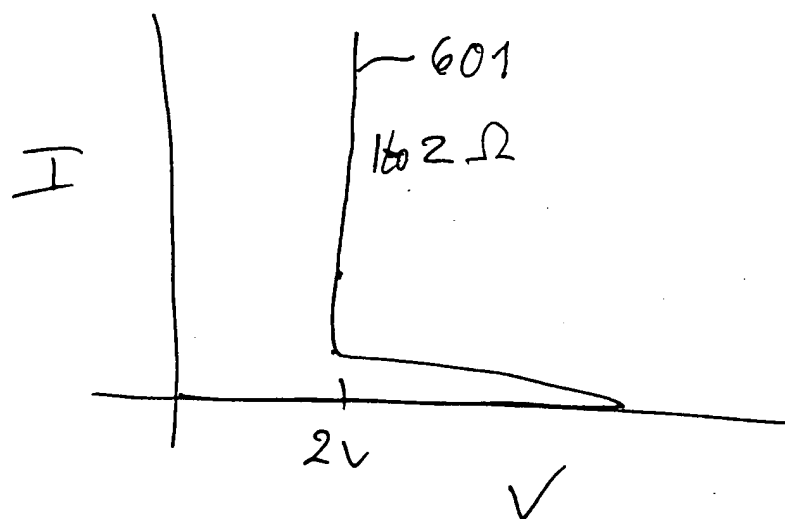


FIG. 6

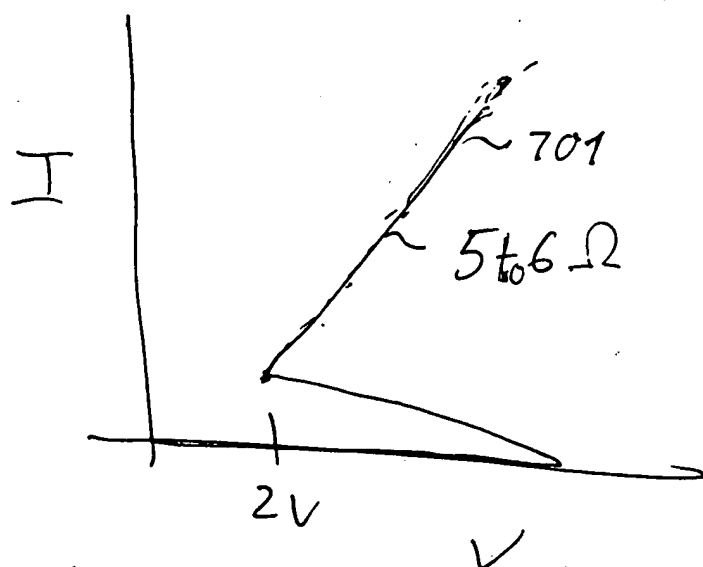


FIG. 7

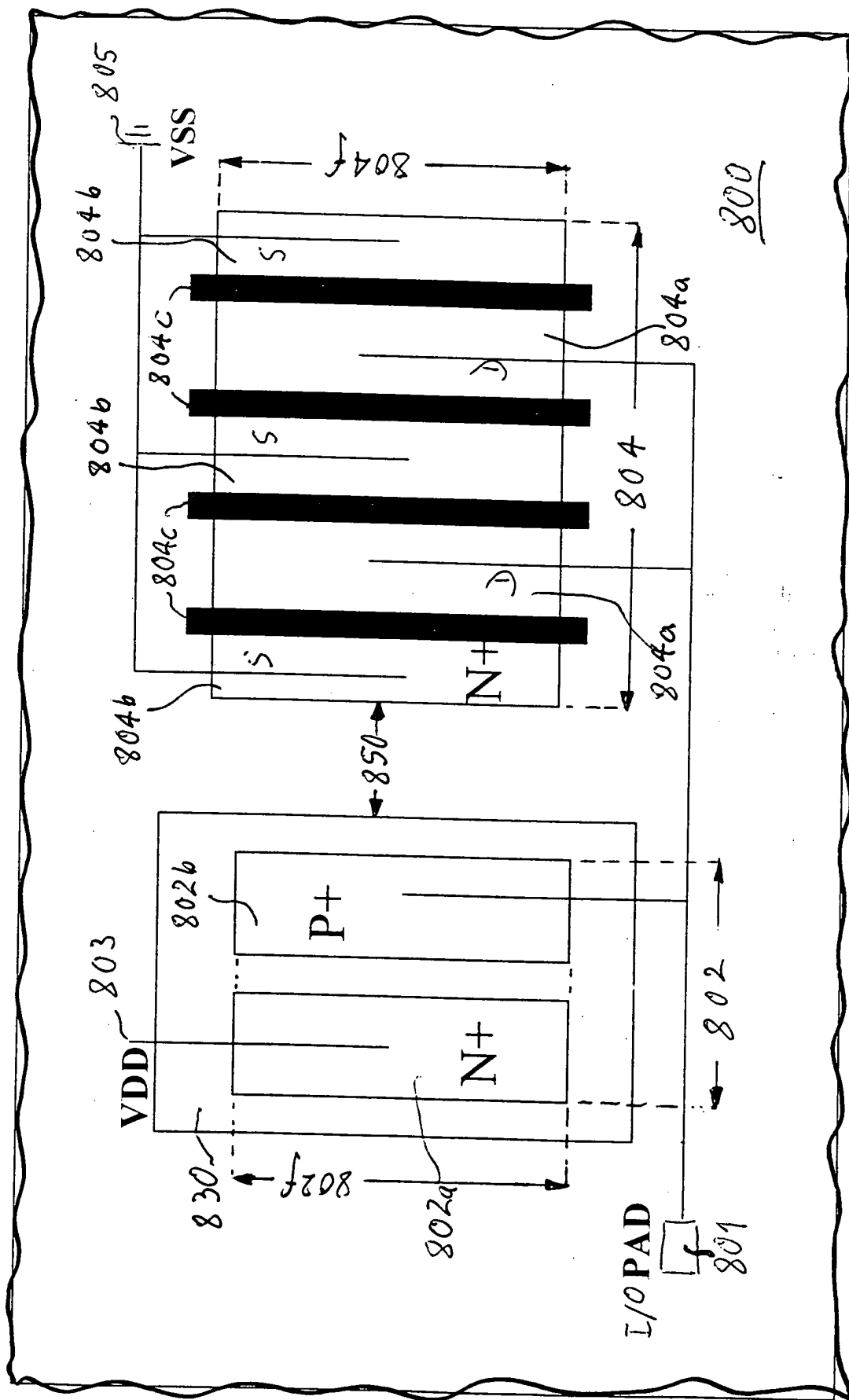


FIG. 8

This diagram shows a cross-sectional view of a semiconductor device. A central channel region 900 is defined by a dashed line. It is flanked by source/drain regions 902, which are labeled P+ and N+. The device is surrounded by guard rings 960, which are labeled P+ Guardring to Vss. The channel region 900 is separated from the guard rings by a distance Y. The source/drain regions 902 are separated from the channel region 900 by a distance X. The guard rings 960 are separated from the channel region 900 by a distance Y. The device is labeled 930.

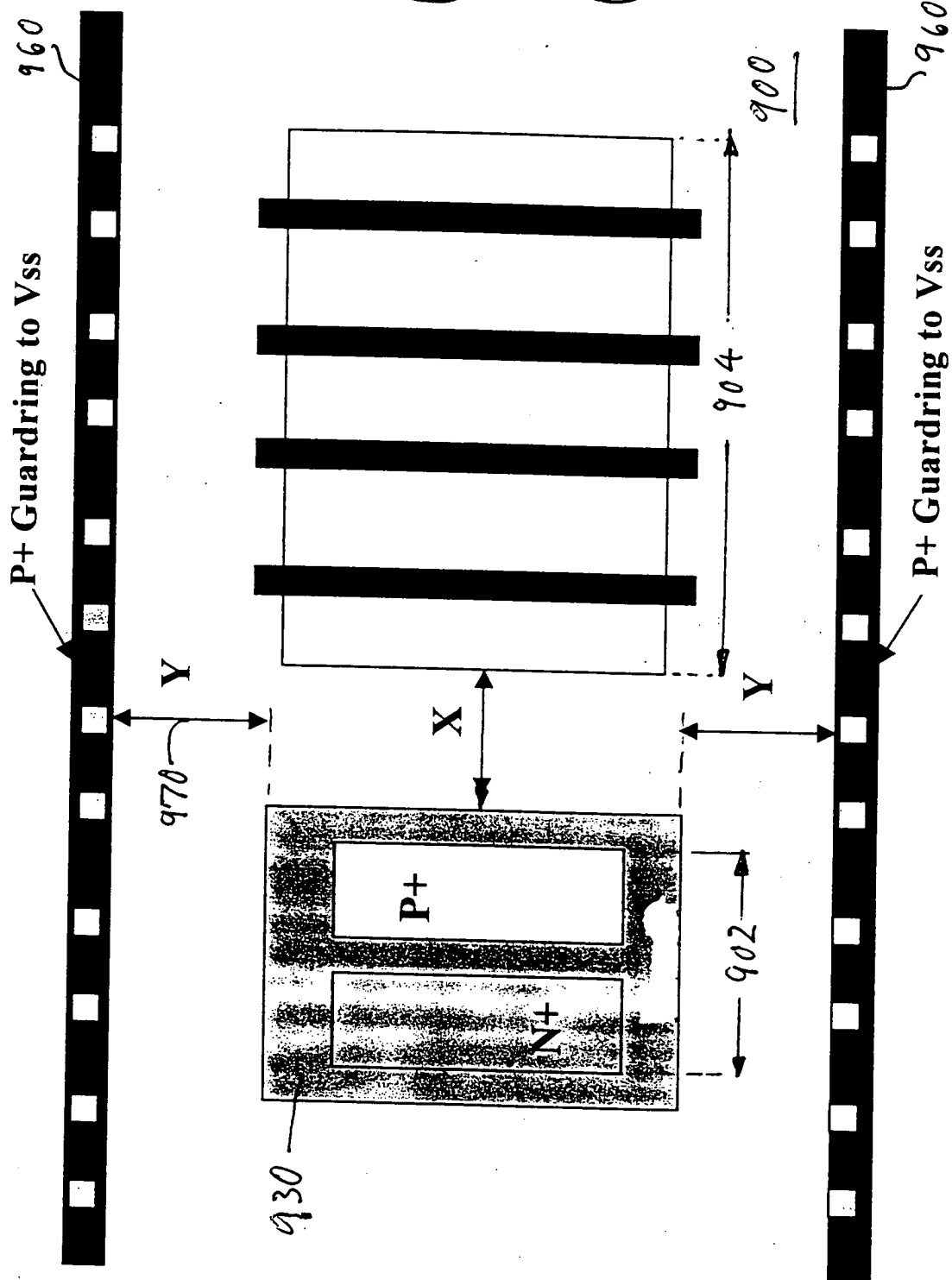
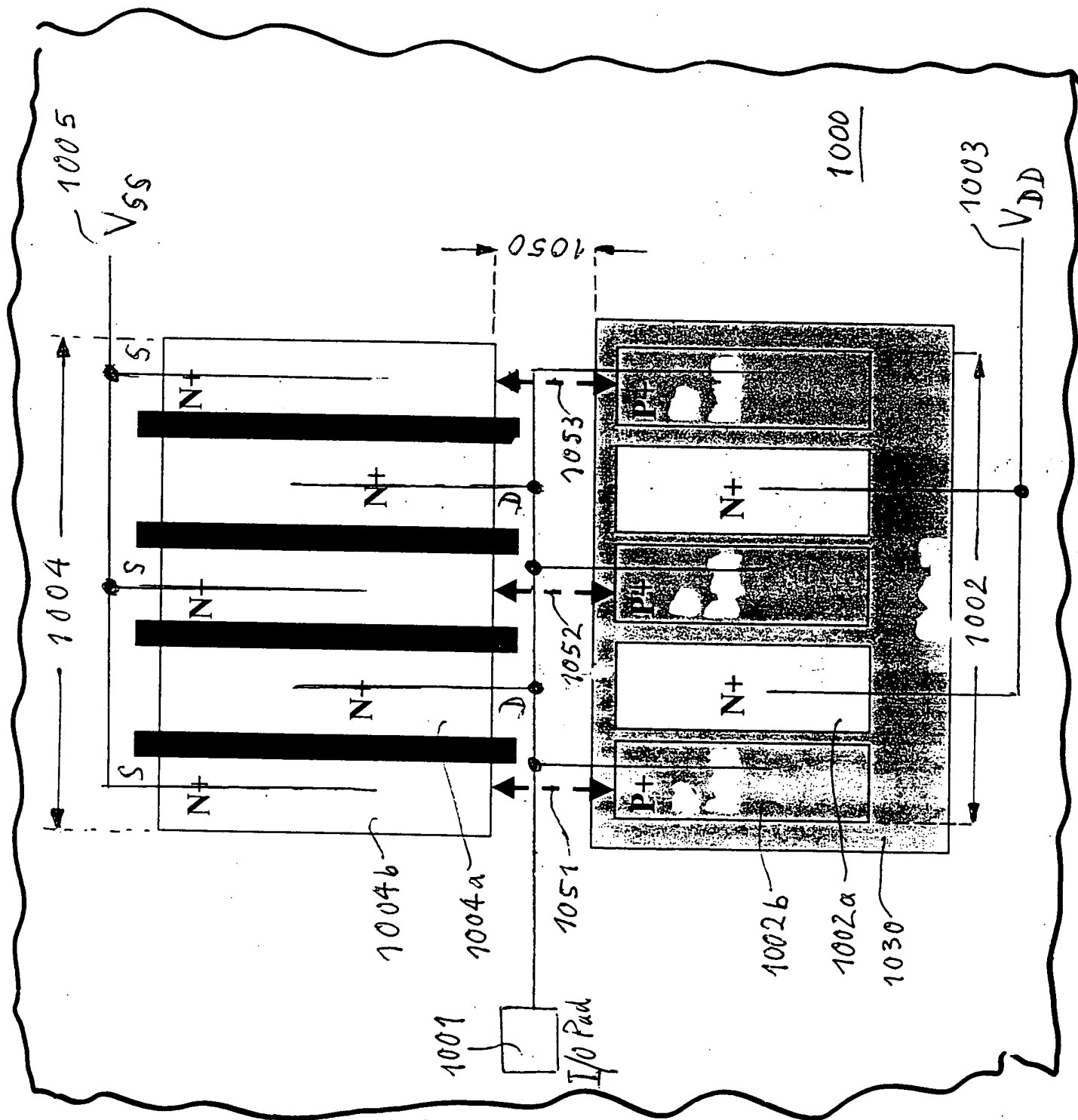


FIG. 10



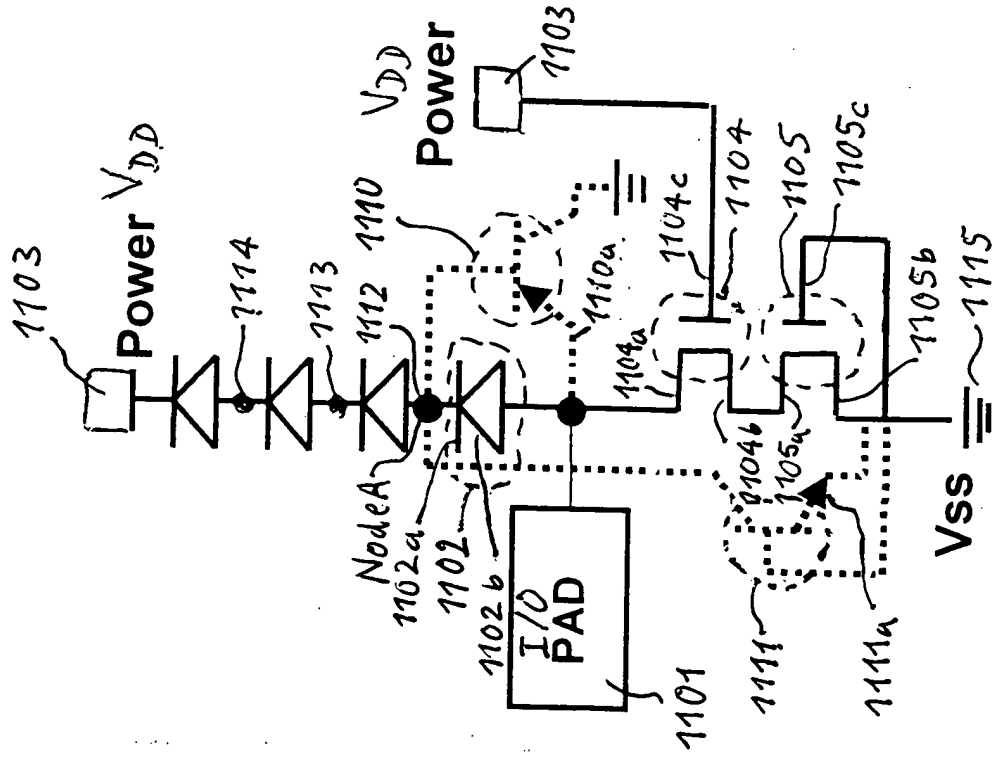


FIG. 11

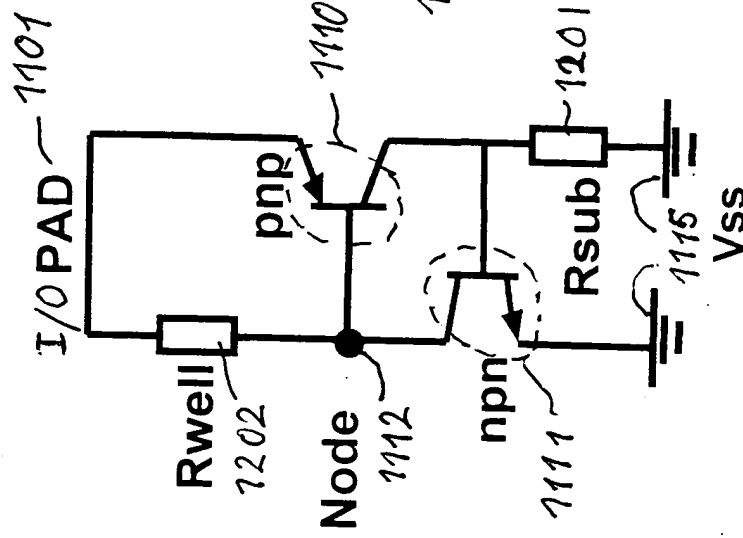


FIG. 12

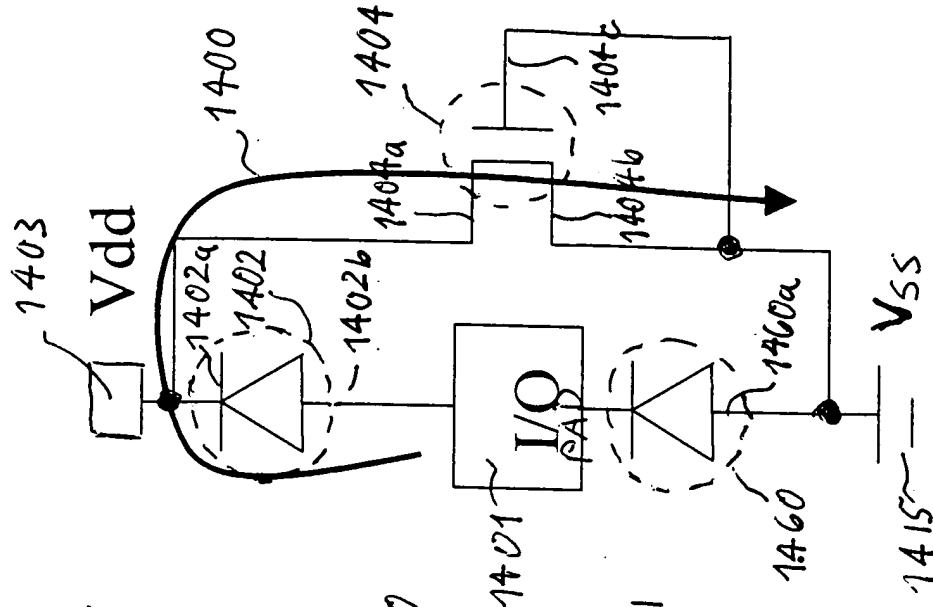


FIG. 14

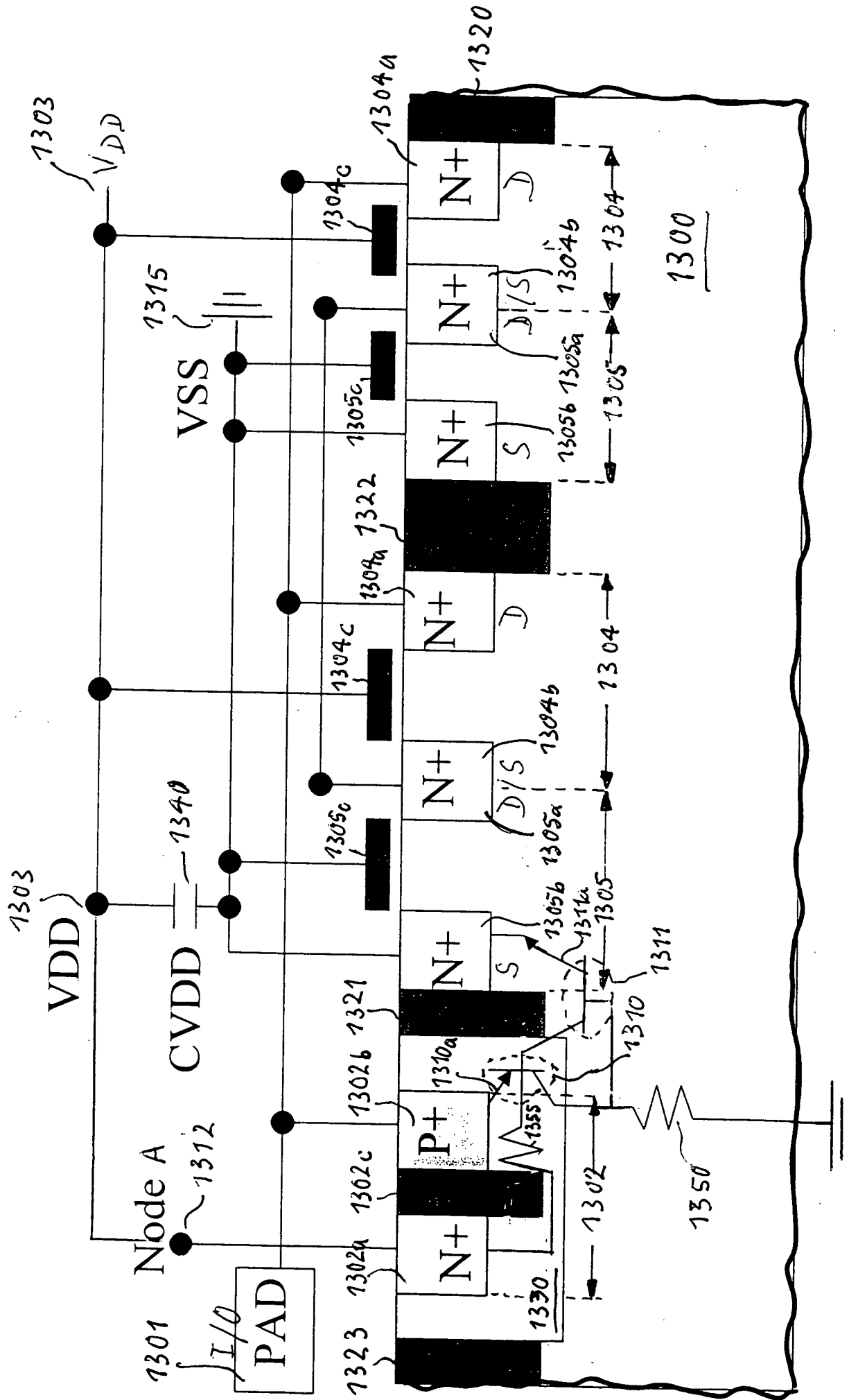


FIG. 13

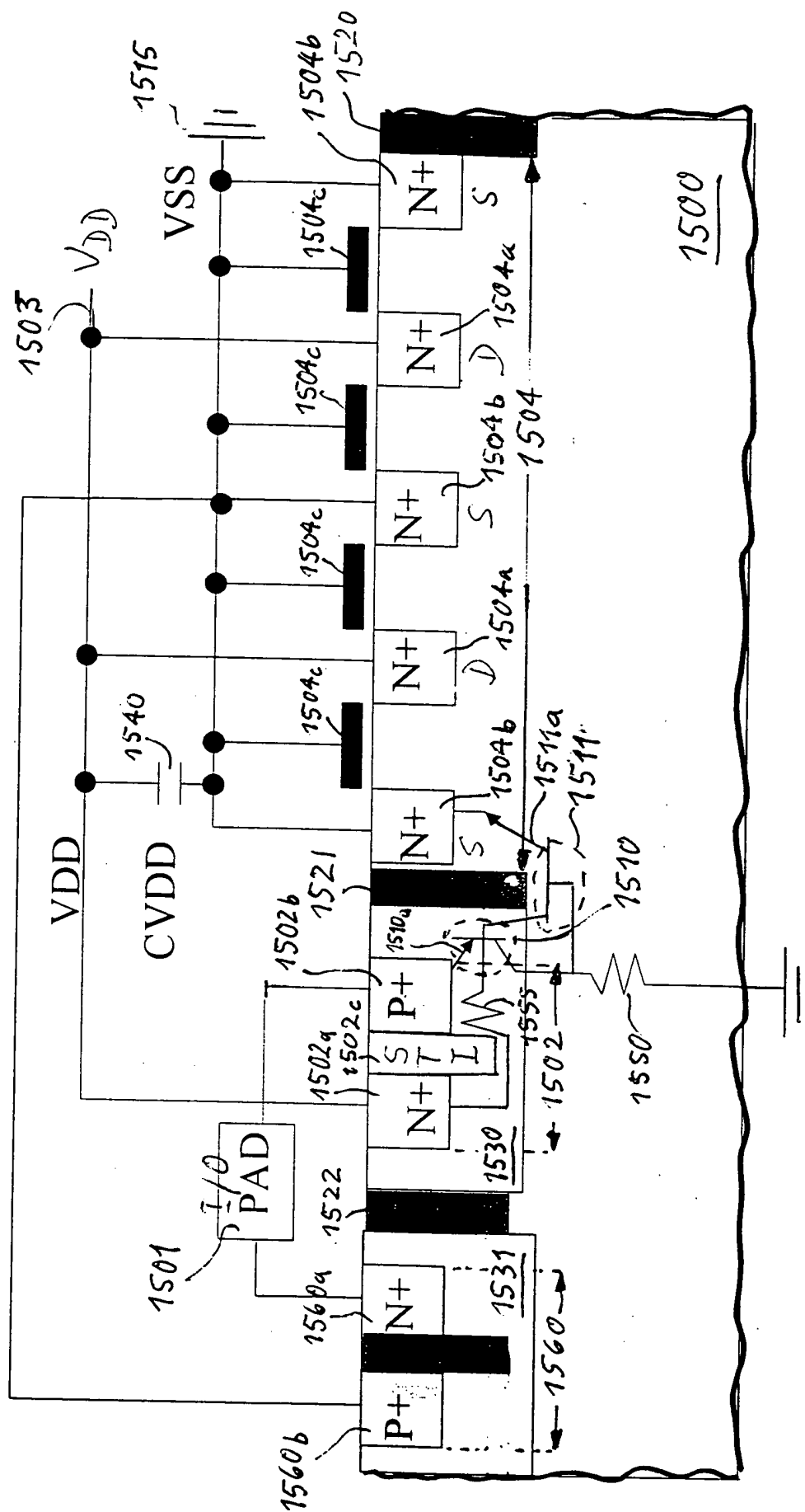


FIG. 75.

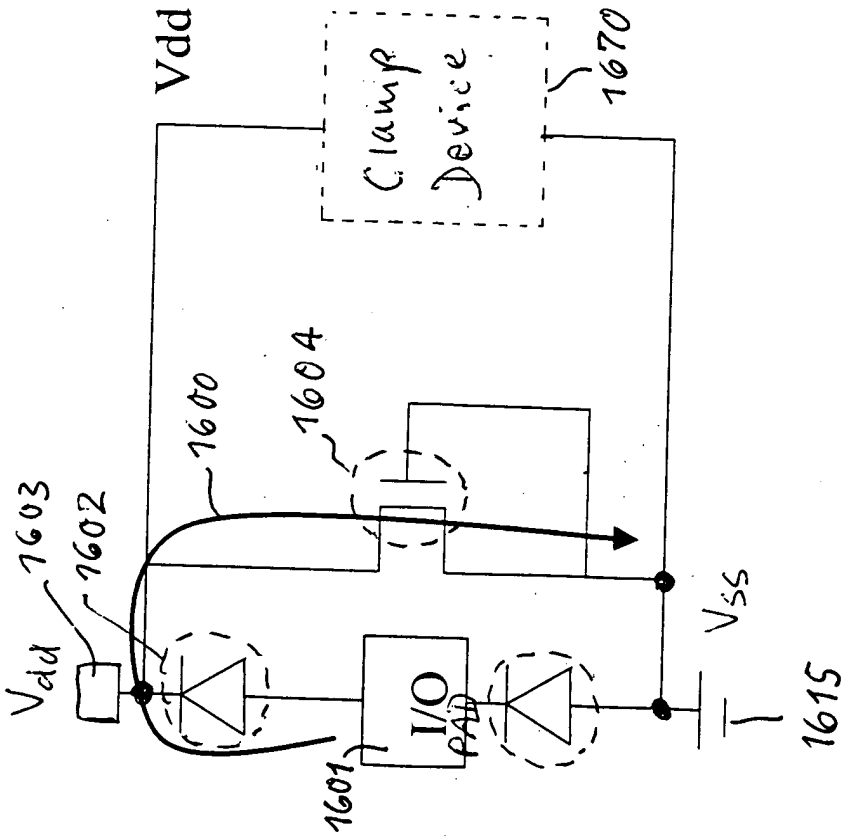


FIG. 16

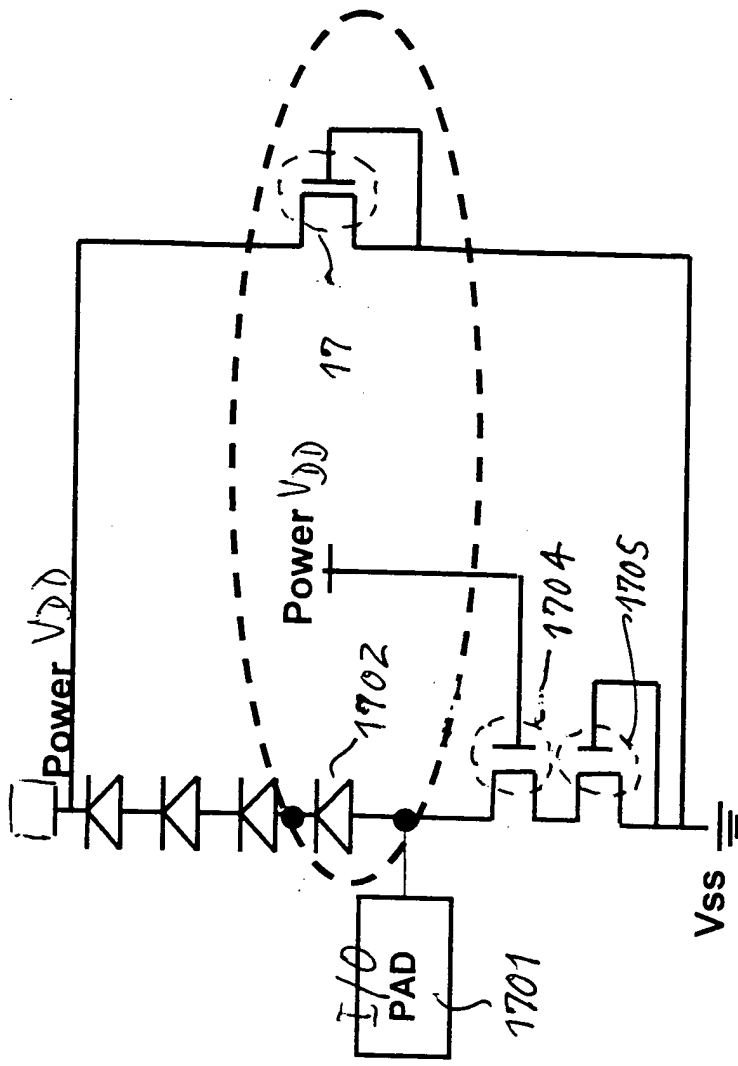


FIG. 17